

ATTACHMENT A -- REVISIONS TO THE SPECIFICATION

This attachment includes paragraphs that are being rewritten in this Amendment, marked up to show the changes in the rewritten paragraphs.

Please rewrite the title of the invention, on page 1, to read as follows:

SEMICONDUCTOR DEVICE HAVING A STEP-LIKE SECTION ON THE BACK SIDE OF THE SUBSTRATE, AND METHOD FOR MANUFACTURING THE SAME.

Please insert following new section on page 1 of the application, between the title and "BACKGROUND OF THE INVENTION":

CROSS REFERENCE TO RELATED APPLICATION

This is a continuation of application number 10/057,099, filed January 29, 2002.

Please rewrite the paragraph at page 1, lines 11-13, so that it reads as follows:

This application is counterpart of Japanese patent [applications] application, Serial Number 250482/2001, filed August 21, 2001, the subject matter of which is incorporated herein by reference.

Please rewrite the paragraph bridging pages 1 and 2, so that it reads as follows:

With [a] size [reduction] reductions in portable [device] devices, there has been a demand for a reduction in the size of [a] semiconductor [device mounted to] devices in the portable device. In order to meet such a demand, a semiconductor device called a "Chip Size Package" having outside dimensions approximately identical to those of a semiconductor chip has come along. As one form of the chip size package, there is known a semiconductor device called a "Wafer Level Chip Size Package" or "Wafer Level Chip Scale Package". In such a wafer level chip size package (hereinafter called "WCSP"), the surface of a semiconductor chip is sealed with a resin, whereas the back (silicon surface) thereof has an exposed structure. In the WCSP, an index mark such as a one pin mark or the like for determining the direction of mounting of the WCSP on a

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printed circuit board is formed on the back (silicon surface) of the exposed semiconductor chip by marking processing. As the marking processing, may be mentioned, for example, a laser mark system for forming each mark by laser processing.

Please rewrite the paragraph at page 2, lines 3-18, so that it reads as follows:

However, the back (silicon surface) of the semiconductor chip is ground to further thin the thickness of the WCSP and due to reasons such as [consideration to] the difference between [a] the linear expansion coefficient of silicon and that of the printed circuit board. [Therefore, the] The silicon surface thereof is held in a mirror state. A problem arises in that even if a laser is used to effect marking on the silicon surface held in such a mirror state, the difference between the intensity of light reflected by a location subjected to the marking and the intensity of light reflected by a location free of the marking is small, i.e., the contrast is low, and hence the recognition of each mark falls into difficulties. The difficulty of recognizing the mark means that the automatic mounting or packaging of the WCSP on the printed circuit board by use of an automatic mounting or packaging device provided with an image recognizer [falls into difficulties] is also difficult. Further, the difficulty of recognizing the mark means that a visual inspecting device with an image recognizer encounters difficulties in determining whether the WCSP is placed in a proper orientation upon a visual inspection done after the packaging of the WCSP on the printed circuit board.

Please rewrite the paragraph at page 6, lines 1-5, so that it reads as follows:

A semiconductor device according to preferred embodiments of the present invention will be explained hereinafter with reference to the figures. In order to simplify the explanation, like elements are given like or corresponding reference numerals through this specification and figures. Dual explanations of the same elements are avoided.

Please rewrite the paragraph at page 6, lines 11-14, so that it reads as follows:

The semiconductor device 101 corresponds to the W CSP as mentioned previously. The semiconductor device 101 has a semiconductor substrate 103 (also called a "semiconductor chip"), [an] a sealing resin 111, and a plurality of protruded electrodes 113.

Please rewrite the paragraph at page 8, lines 2-9, so that it reads as follows:

The metal wiring layers 303 performs the function of substantially shifting the positions of external terminals from a peripheral portion of the semiconductor substrate 103 to a central area of the semiconductor substrate 103. In general, such shift is called "relocation". Therefore, the metal wiring layers 303, which perform such shift, are called "relocating wirings or rewirings". They may also be known as "redistribution" conductors. Placing the protruded electrodes 113 serving as the external terminals in the central area of the semiconductor substrate 103 in this way allows a size reduction in the printed circuit board connected to the semiconductor device 101.

Please rewrite the paragraph at page 8, lines 12-17, so that it reads as follows:

Unillustrated plural circuit elements are formed on a surface 109 (first main surface) of a semiconductor substrate 103 made up of silicon. A steplike section 107 is provided at the back 105 (second main surface) of the semiconductor substrate 103. An insulating layer 402 having contact holes (not shown) [are] is formed over the respective circuit elements. An unillustrated conductive layer is formed inside each contact hole.